

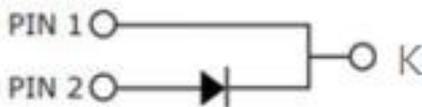
## S3D12065A 650V SiC POWER SCHOTTKY RECTIFIERS



### Description

S3D12065A is SiC Schottky rectifiers packaged in TO-220AC(TO-220-2) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D12065A is ideal for energy sensitive, high frequency applications in challenging environments.

### Circuit Diagram



### Features

- 175°C TJ operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

### Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	650	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_{DC}$			
Average Rectified Forward Current	$I_{F(AV)1}$	@Tc=25°C	48	A
	$I_{F(AV)2}$	@Tc=157°C	12	A
Repetitive Peak Forward Surge Current	$I_{FRM1}$	10ms, Half Sine pulse, Tc=25°C	60	A
	$I_{FRM2}$	10ms, Half Sine pulse, Tc=110°C	40	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM1}$	10ms, Half Sine pulse, Tc=25°C	140	A
	$I_{FSM2}$	10ms, Half Sine pulse, Tc=110°C	96	A
Non-Repetitive Peak Forward Surge Current	$I_{F,Max1}$	10µs. Pulse, Tc=25°C	1200	A
	$I_{F,Max2}$	10µs. Pulse, Tc=110°C	100	A
Power Dissipation	$P_{tot1}$	Tc=25°C	143	W
	$P_{tot2}$	Tc=110°C	62	W

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 12A, Pulse, T <sub>J</sub> = 25 °C	1.5	1.7	V
	V <sub>F2</sub>	@ 12A, Pulse, T <sub>J</sub> = 175 °C	1.75	2.2	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.1	6	uA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 175 °C	1.5	50	uA
Junction Capacitance	C <sub>T</sub>	V <sub>R</sub> =0V, T <sub>J</sub> =25°C, f=1MHz	764	-	pF
Reverse Recovery Charge	Q <sub>c</sub>	I <sub>F</sub> = 12A, di/dt = 200A/μs V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C	84.07	-	nC
Capacitance Stored Energy	EC	V <sub>R</sub> = 400 V, T <sub>J</sub> =25°C	17.30	-	μJ

\* Pulse width < 300 μs, duty cycle < 2%

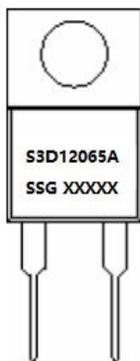
### Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	DC operation	1.05	°C/W

### Ordering Information

Device	Package	Shipping
S3D12065A	TO-220AC(TO-220-2)	50pcs / tube

### Marking Diagram



Where XXXXX is YYWWL

S3D = Device Type  
A = Package type  
12 = Forward Current (12A)  
065 = Reverse Voltage (650V)  
SSG = SSC  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ratings and Characteristics Curves**

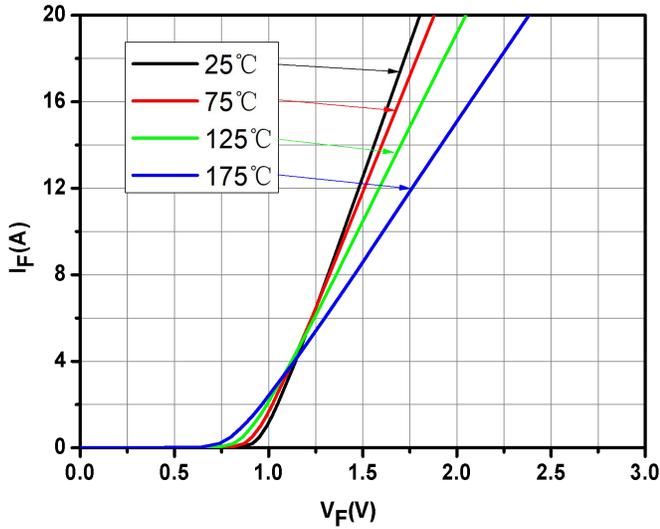


Fig.1-Typical Forward Voltage Characteristics

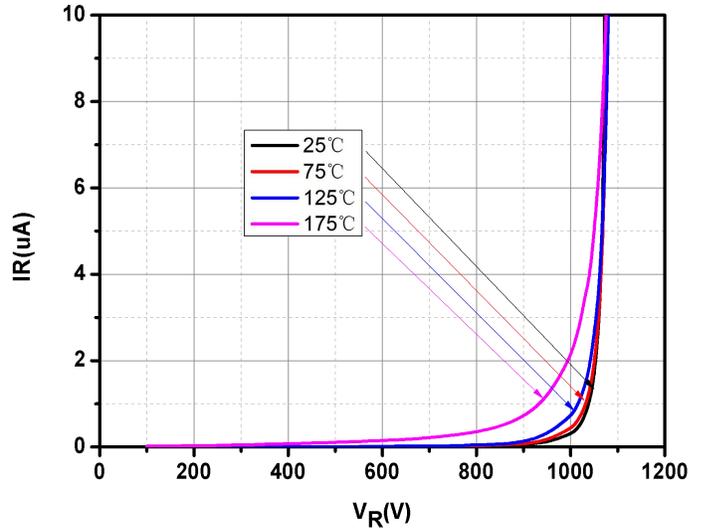


Fig.2-Typical Reverse Characteristics

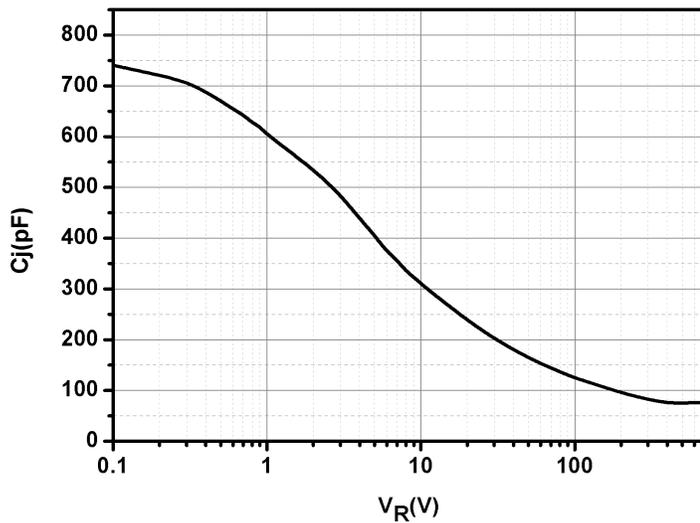


Fig.3-Capacitance vs. Reverse Voltage

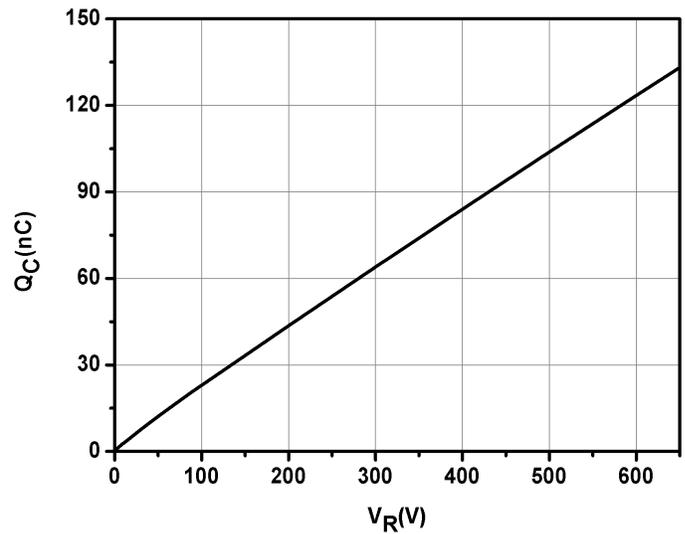


Fig.4-Total Capacitance Charge vs. Reverse Voltage

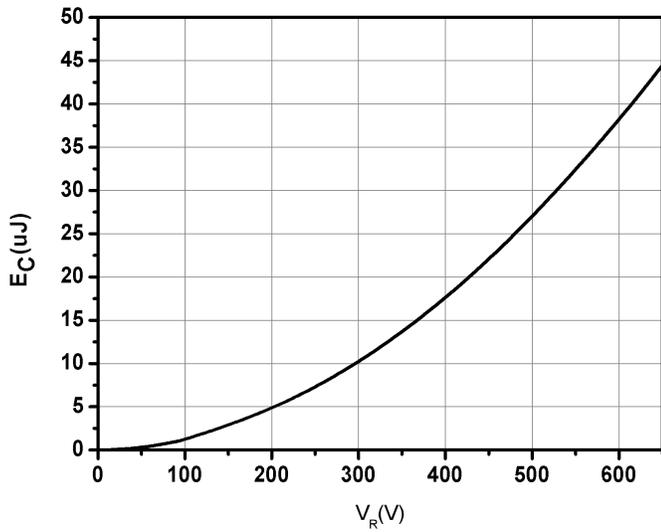


Fig.5-Capacitance Stored Energy

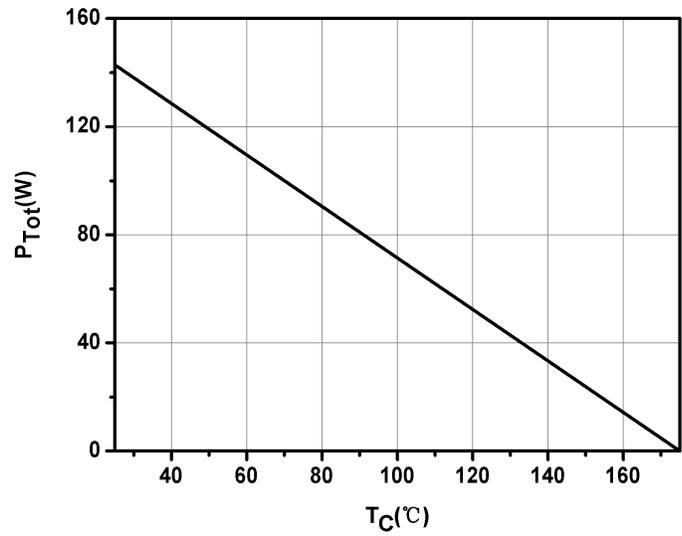


Fig.6-Power Derating

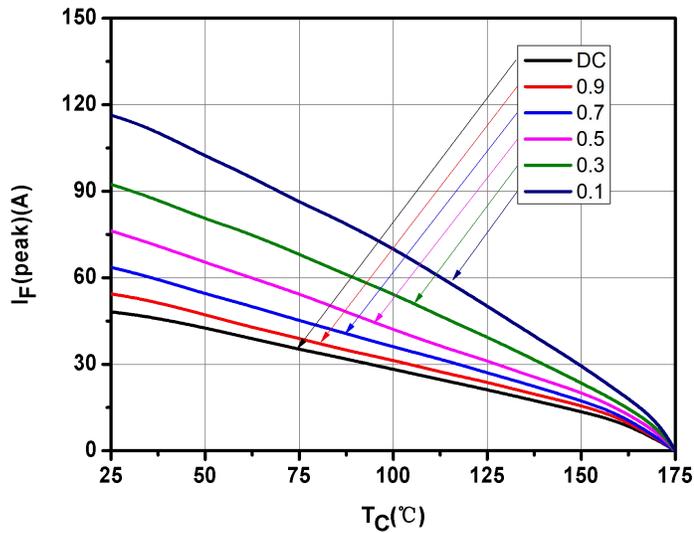
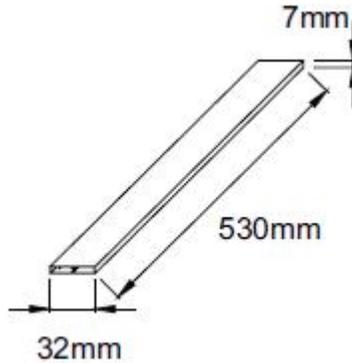
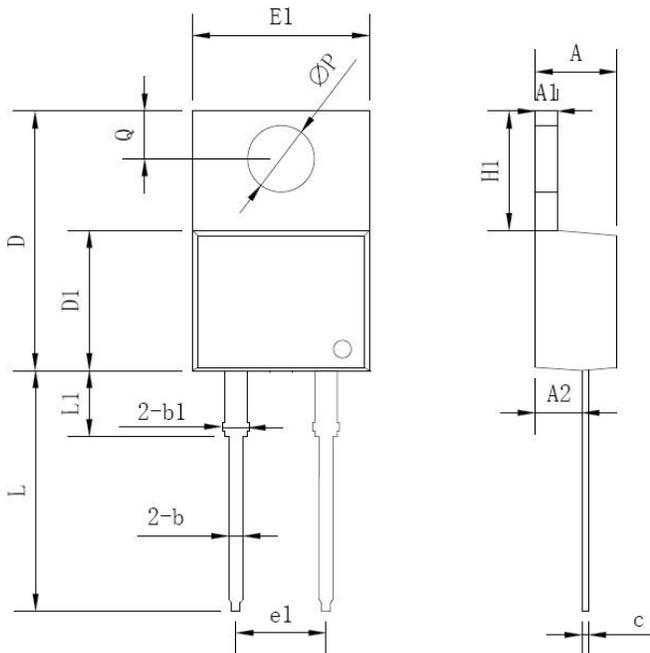


Fig.7-Current Derating

**Tube Specification(TO-220-2)**



**Mechanical Dimensions TO-220AC(TO-220-2)**



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	3.56	-	4.83
A1	0.51	-	1.40
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
c	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E1	9.65	10.16	10.67
e1	-	5.08	-
H1	5.84	-	6.86
L	12.70	-	14.73
L1	-	-	6.35
$\phi P$	-	3.56	-
Q	2.54	-	3.43

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